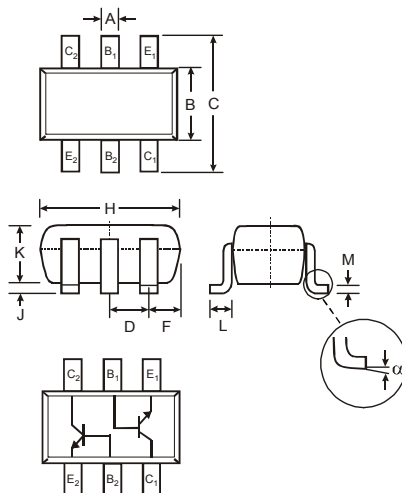


Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMDT2907A)
- **Lead Free/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3 and 4)**

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe)
- Terminal Connections: See Diagram
- Marking Information: K1P, See Page 4
- Ordering & Date Code Information: See Page 4
- Weight: 0.006 grams (approximate)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	75	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous (Note 1)	I _C	600	mA
Total Power Dissipation (Note 1)	P _d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. No purposefully added lead.
 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 4. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	75	—	V	I _C = 10μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	40	—	V	I _C = 10mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0	—	V	I _E = 10μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	10	nA μA	V _{CB} = 60V, I _E = 0 V _{CB} = 60V, I _E = 0, T _A = 150°C
Collector Cutoff Current	I _{CEX}	—	10	nA	V _{CE} = 60V, V _{EB(OFF)} = 3.0V
Emitter Cutoff Current	I _{EBO}	—	10	nA	V _{EB} = 3.0V, I _C = 0
Base Cutoff Current	I _{BL}	—	20	nA	V _{CE} = 60V, V _{EB(OFF)} = 3.0V
ON CHARACTERISTICS (Note 5)					
DC Current Gain	h _{FE}	35 50 75 100 40 50 35	— — — 300 — — —	—	I _C = 100μA, V _{CE} = 10V I _C = 1.0mA, V _{CE} = 10V I _C = 10mA, V _{CE} = 10V I _C = 150mA, V _{CE} = 10V I _C = 500mA, V _{CE} = 10V I _C = 10mA, V _{CE} = 10V, T _A = -55°C I _C = 150mA, V _{CE} = 1.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	0.3 1.0	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.6 —	1.2 2.0	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	8	pF	V _{CB} = 10V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{ibo}	—	25	pF	V _{EB} = 0.5V, f = 1.0MHz, I _C = 0
Current Gain-Bandwidth Product	f _T	300	—	MHz	V _{CE} = 20V, I _C = 20mA, f = 100MHz
Noise Figure	NF	—	4.0	dB	V _{CE} = 10V, I _C = 100μA, R _S = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	—	10	ns	V _{CC} = 30V, I _C = 150mA, V _{BE(off)} = -0.5V, I _{B1} = 15mA
Rise Time	t _r	—	25	ns	
Storage Time	t _s	—	225	ns	V _{CC} = 30V, I _C = 150mA, I _{B1} = I _{B2} = 15mA
Fall Time	t _f	—	60	ns	

Notes: 5. Short duration pulse test used to minimize self-heating effect.

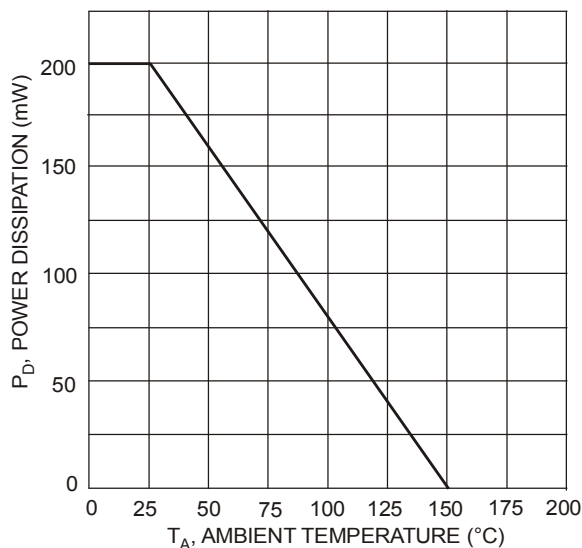


Fig. 1, Max Power Dissipation vs. Ambient Temperature

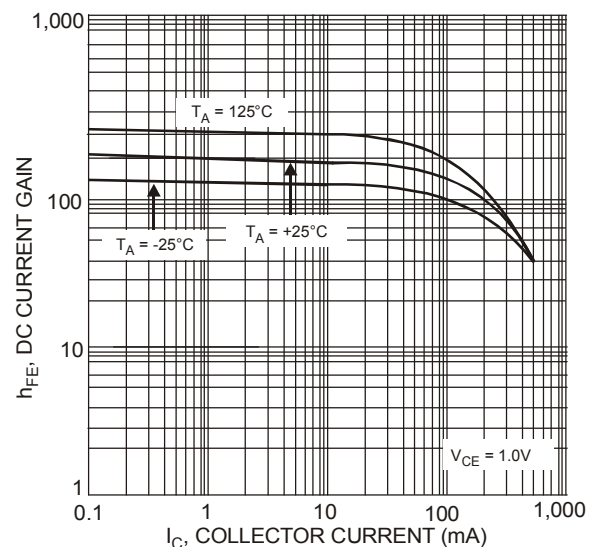


Fig. 2, Typical DC Current Gain vs. Collector Current

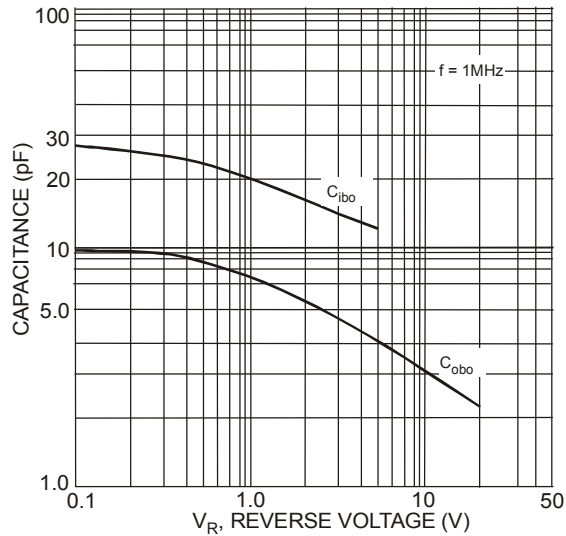


Fig. 3, Typical Capacitance Characteristics

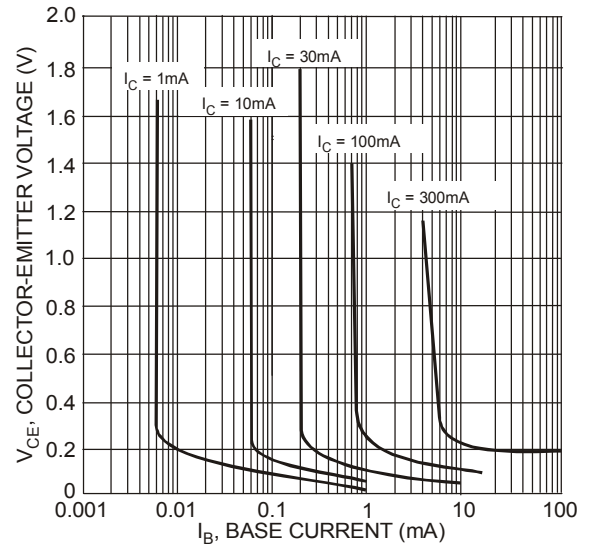


Fig. 4, Typical Collector Saturation Region

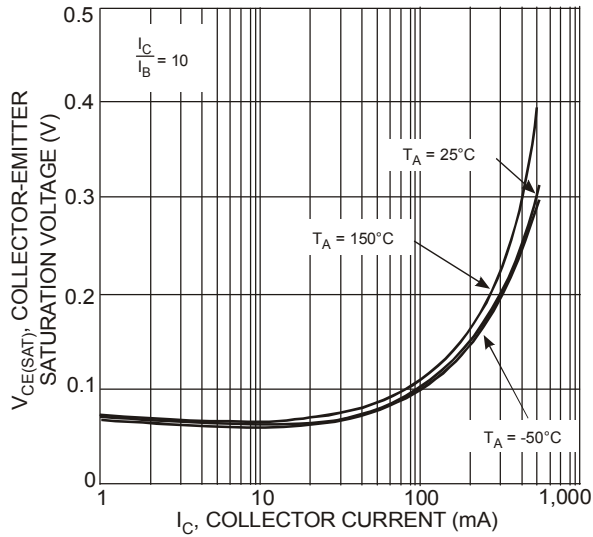


Fig. 5, Typical Collector-Emitter Saturation Voltage vs. Collector Current

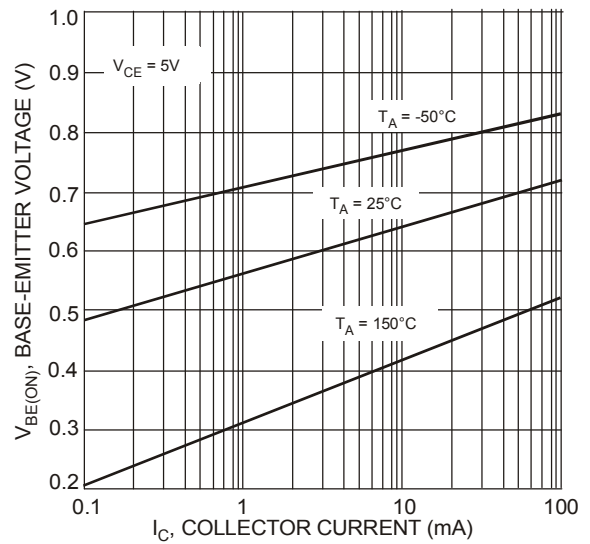


Fig. 6, Typical Base-Emitter Voltage vs. Collector Current

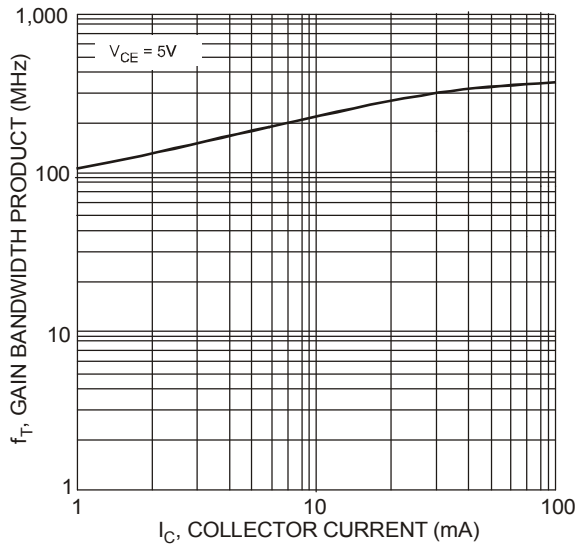


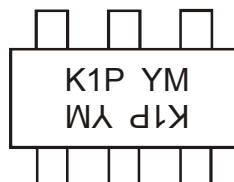
Fig. 7, Typical Gain Bandwidth Product vs. Collector Current

Ordering Information (Note 6)

Device	Packaging	Shipping
MMDT2222A-7-F	SOT-363	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



K1P = Product Type Marking Code

YM = Date Code Marking

Y = Year ex: N = 2002

M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	M	N	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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